TAS5634 300W 立体声/600W 单声道高清数字输入、58V D 类放大器功率级

1 特性

- PWM 输入、D 类放大器功率级，与 TI 数字输入 (I2S) 音频处理器和调制器兼容
- 高清集成闭环反馈，具备以下特性：
  - 在为 6Ω 负载提供 1W 功率时，THD 为 0.025%
  - PSRR 大于 70dB（无输入信号）
  - SNR 大于 105dB（A 加权）
- 10% THD+N 时的输出功率
  - 600W/3Ω（PBTL 单声道配置）
  - 300W/6Ω（BTL 立体声配置）
  - 230W/8Ω（BTL 立体声配置）
- 1% THD+N 时的输出功率
  - 465W/3Ω（PBTL 单声道配置）
  - 240W/6Ω（BTL 立体声配置）
  - 180W/8Ω（BTL 立体声配置）
- 集成式 80 mΩ MOSFET，可降低散热器尺寸
  - 满量程输出功率下的效率大于 91%
  - 1/8 量程输出功率下的效率大于 75%
- 启动时无喀哒声
- 器件保护：欠压保护、过热保护、过流保护、短路保护和直流扬声器保护
- 适用于 G 类电源控制的预削波输出信号
- 44 引脚 HTSSOP (DDV) 封装，顶部带有散热焊盘

2 应用

- 电动扬声器
- 低音炮
- 微型组件系统
- 条形音箱
- 专业和公共广播 (PA) 扬声器

3 说明

TAS5634 是一款 PWM 输入 D 类放大器功率级，可在 58V 标称电源电压下提供 2 x 300W (6Ω) 或 1 x 600W (3Ω) 的输出功率。58V 电源电压支持较高阻抗的扬声器负载，其中 BTL 为 6Ω，PBTL 为 3Ω。集成式 MOSFET 和全新栅极驱动方案具有较高的峰值效率和较低的空闲损耗，能够减小散热器解决方案尺寸。

TAS5634 使用闭环反馈设计，具有恒定的电压增益。开关模式电源 (SMPS) 的使用，使得内部匹配的增益电阻器可确保实现较高的电源抑制比 (PSRR) 和较低的输出噪声。

TAS5634 是一款兼容 TI 的数字输入 (I2S) 音频处理器和调制器产品组合的全集成式功率级，与 TAS5548 和 TAS5558 类似，也是一个完整的数字输入 D 类放大器。TAS5634 采用表面安装 44 引脚 HTSSOP 封装，是 PWM 输入 D 类功率级兼容引脚产品系列（包括 TAS5612LA、TAS5614LA 和 TAS5624A）中的一员。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TAS5634	HTSSOP	14.00mm x 6.10mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化电路原理图

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

目录

1 特性 ... 1
2 应用 ... 1
3 说明 ... 1
4 修订历史记录 ... 2
5 **Device Comparison** ... 3
6 **Pin Configuration and Functions** ... 4
7 **Specifications** ... 7
7.1 Absolute Maximum Ratings ... 7
7.2 ESD Ratings ... 7
7.3 Recommended Operating Conditions ... 8
7.4 Thermal Information ... 8
7.5 Audio Specification Stereo (BTL) ... 9
7.6 Audio Specifications Mono (PBTL) ... 9
7.7 Audio Specification 4 Channels (SE) ... 10
7.8 Electrical Characteristics ... 11
7.9 Typical Characteristics ... 12
8 **Detailed Description** ... 16
8.1 Overview ... 16
8.2 Functional Block Diagrams ... 17
8.3 Feature Description ... 19
8.4 Device Functional Modes ... 26
9 **Application and Implementation** ... 29
9.1 Application Information ... 29
9.2 Typical Applications ... 29
10 **Power Supply Recommendations** ... 36
10.1 Power Supplies ... 36
10.2 Bootstrap Supply ... 36
11 **Layout** ... 37
11.1 Layout Guidelines ... 37
11.2 Layout Example ... 39
12 器件和文档支持 ... 41
12.1 接收文档更新通知 ... 41
12.2 社区资源 ... 41
12.3 商标 ... 41
12.4 静电放电警告 ... 41
12.5 Glossary ... 41
13 机械、封装和可订购信息 ... 41

4 修订历史记录

日期	修订版本	说明
2017 年 10 月	*	首次公开发布。

Copyright © 2017, Texas Instruments Incorporated

5 Device Comparison

DEVICE NAME	DESCRIPTION	PVDD VOLTAGE (Nom.)	$R_{Drain\text{-}to\text{-}Source}$
TAS5612LA	125 W Stereo / 250 W Mono HD Digital-Input Power Stage	32.5 V	60 mΩ
TAS5614LA	150 W Stereo / 300 W Mono HD Digital-Input Power Stage	36 V	60 mΩ
TAS5624A	200 W Stereo / 400 W Mono HD Digital-Input Power Stage	36 V	40 mΩ
TAS5634	300 W Stereo / 600 W Mono HD Digital-Input Power Stage	58 V	80 mΩ

Copyright © 2017, Texas Instruments Incorporated

6 Pin Configuration and Functions

The TAS5634 is available in a thermally-enhanced, 44-Pin HTSSOP package (DDV).

The package contains a PowerPAD™ that is located on the top side of the device for convenient thermal coupling to a heatsink.

DDV Package
44 Pin (HTSSOP)
Top View

Not to scale

Copyright © 2017, Texas Instruments Incorporated

Pin Functions

PIN		I/O/P[1]	DESCRIPTION	Sections
NAME	NO.			
AVDD	13	P	Analog internal voltage regulator output. Place 1 μF capacitor to GND.	VDD Supply, Internal Regulators (DVDD and AVDD)
BST_A	44	P	Bootstrap pin, A-side. Connect 0.33 nF ceramic capacitor to OUT_A.	BST, Bootstrap Supply
BST_B	43	P	Bootstrap pin, B-side. Connect 0.33 nF ceramic capacitor to OUT_B.	BST, Bootstrap Supply
BST_C	24	P	Bootstrap pin, C-side. Connect 0.33 nF ceramic capacitor to OUT_C.	BST, Bootstrap Supply
BST_D	23	P	Bootstrap pin, D-side. Connect 0.33 nF ceramic capacitor to OUT_D.	BST, Bootstrap Supply
$\overline{\text{CLIP}}$	18	O	Clipping warning; open drain; active low. Connect 10 kΩ pull-up resistor to DVDD to monitor. If unused, do not connect.	Error Reporting
C_START	7	O	Startup ramp timing control pin. Connect capacitor to ground. 330nF for BTL / PBTL mode. 1 μF for SE mode.	Startup and Shutdown Ramp Sequence (C_START)
DVDD	8	P	Digital internal voltage regulator output. Place 1 μF capacitor to GND.	VDD Supply, Internal Regulators (DVDD and AVDD)
$\overline{\text{FAULT}}$	16	O	Fault signal output, open drain; active low. Connect 10 kΩ pull-up resistor to DVDD to monitor. If unused, do not connect.	Error Reporting
GND	9, 10, 11, 12, 25, 26, 33, 34, 41, 42	P	Ground.	
GVDD_AB	1	P	Gate-drive voltage supply; AB-side. Place 100 nF decoupling capacitor to GND.	GVDD, Gate-Drive Power Supply
GVDD_CD	22	P	Gate-drive voltage supply; CD-side. Place 100 nF decoupling capacitor to GND.	GVDD, Gate-Drive Power Supply
INPUT_A	5	I	PWM Input signal for half-bridge A. If unused, connect INPUT_A to GND.	
INPUT_B	6	I	PWM Input signal for half-bridge B. If unused, connect INPUT_B to GND.	
INPUT_C	14	I	PWM Input signal for half-bridge C. If unused, connect INPUT_C to GND.	
INPUT_D	15	I	PWM Input signal for half-bridge D. If unused, connect INPUT_D to GND.	
M1	19	I	Mode selection 1.	Device Functional Modes
M2	20	I	Mode selection 2.	Device Functional Modes
M3	21	I	Mode selection 3.	Device Functional Modes
OC_ADJ	3	O	Over-Current threshold programming pin. Connect programming resistor to GND. Use 27 kΩ for typical applications.	Overload and Short Circuit Current Protection
$\overline{\text{OTW}}$	17	O	Over-temperature warning; open drain; active low. Connect 10 kΩ pull-up resistor to DVDD to monitor. If unused, do not connect.	Error Reporting
OUT_A	39, 40	O	Output, half-bridge A. If unused, remove BST_A capacitor and GND INPUT_A pin. Output pins can be left floating.	
OUT_B	35	O	Output, half-bridge B. If unused, remove BST_B capacitor and GND INPUT_B pin. Output pins can be left floating.	
OUT_C	32	O	Output, half-bridge C. If unused, remove BST_C capacitor and GND INPUT_C pin. Output pins can be left floating.	
OUT_D	27, 28	O	Output, half-bridge D. If unused, remove BST_D capacitor and GND INPUT_D pin. Output pins can be left floating.	
PVDD_AB	36, 37, 38	P	PVDD supply for half-bridge A and B. Place a minimum of 1 μF decoupling capacitor near PVDD_AB pin.	PVDD, Output Stage Power Supply
PVDD_CD	29, 30, 31	P	PVDD supply for half-bridge C and D. Place a minimum of 1 μF decoupling capacitor near PVDD_CD pin.	PVDD, Output Stage Power Supply
$\overline{\text{RESET}}$	4	I	Device reset pin; active low.	Device Reset

(1) I = Input, O = Output, P = Power

Copyright © 2017, Texas Instruments Incorporated

Pin Functions (continued)

PIN		I/O/P(1)	DESCRIPTION	Sections
NAME	NO.			
VDD	2	P	12V power supply input for internal analog and digital voltage regulators.	VDD Supply, Internal Regulators (DVDD and AVDD)
PowerPAD™		P	Ground, connect to grounded heat sink.	

Table 1. Mode Selection Pins

MODE PINS			PWM Input(1)	Output Configuration	Input A	Input B	Input C	Input D	DC Speaker Protection(2)	Mode	C_START Capacitor
M3	M2	M1									
0	0	0	2N	2 x BTL	PWMa	PWMb	PWMc	PWMd	Enabled	AD	330 nF
0	0	1	1N(3)	2 x BTL	PWMa	Unused	PWMc	Unused	Enabled	AD	330 nF
0	1	0	2N	2 x BTL	PWMa	PWMb	PWMc	PWMd	Disabled	AD or BD	330 nF
0	1	1	2N/1N(3)	1 x BTL + 2 x SE(4)	PWMa	PWMb	PWMc	PWMd	Enabled (BTL only)	AD	1 μF
1	0	0	2N	1 x PBTL	PWMa	PWMb	0	0	Enabled	AD	330 nF
1	0	0	1N(3)	1 x PBTL	PWMa	Unused	0	1	Enabled	AD	330 nF
1	0	0	2N	1 x PBTL	PWMa	PWMb	1	0	Disabled	AD or BD	330 nF
1	0	1	1N1	4 x SE(5)	PWMa	PWMb	PWMc	PWMd	Disabled	AD	1 μF

(1) The 1N and 2N naming convention is used to indicate the number of PWM lines to the power stage per channel in a specific mode.
(2) DC Speaker Protection is disabled in BD mode due to in phase inductor ripple current.
(3) Using 1N interface in BTL and PBTL mode results in increased DC offset on the output terminals.
(4) In [011] 1 x BTL + 2 x SE mode, Output A and B refers to the BTL channel, and Output C and D the SE channels
(5) The 4xSE mode can be used as 1 x BTL + 2 x SE configuration by feeding a 2N PWM signal to either INPUT_AB or INPUT_CD

Copyright © 2017, Texas Instruments Incorporated

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted (1)

	MIN	MAX	UNIT
VDD to GND, GVDD_X(2) to GND	–0.3	13.2	V
PVDD_X(2) to GND	–0.3	65	V
PVDD_X(2) to GND(3) (Less than 8ns transient)	-0.3	71	V
OUT_X to GND	-0.3	65	V
OUT_X to GND(3) (Less than 8ns transient)	-7	71	V
BST_X to OUT_X(4)	–0.3	13.2	V
DVDD to GND	–0.3	4.2	V
AVDD to GND	–0.3	8.5	V
OC_ADJ, M1, M2, M3, C_START, INPUT_X to GND	–0.3	4.2	V
$\overline{\text{RESET}}$, $\overline{\text{FAULT}}$, $\overline{\text{OTW}}$, $\overline{\text{CLIP}}$, to GND	–0.3	4.2	V
Maximum continuous sink current ($\overline{\text{FAULT}}$, $\overline{\text{OTW}}$, $\overline{\text{CLIP}}$)		9	mA
Maximum operating junction temperature range, T_J	0	150	°C
Storage temperature, T_{stg}	–40	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) GVDD_X and PVDD_X represents a full bridge gate drive or power supply. GVDD_X is GVDD_AB or GVDD_CD, PVDD_X is PVDD_AB or PVDD_CD
(3) These voltages represents the DC voltage + peak AC waveform measured at the terminal of the device in all conditions.
(4) Maximum BST_X to GND voltage is the sum of maximum PVDD to GND and GVDD to GND voltages minus a diode drop.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1) (2)	±2000	V
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101(3) (2)	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) Maximum BST_X to GND voltage is the sum of maximum PVDD to GND and GVDD to GND voltages minus a diode drop.
(3) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Copyright © 2017, Texas Instruments Incorporated

7.3 Recommended Operating Conditions

				MIN	TYP	MAX	UNIT
PVDD_X	Full-bridge supply		DC supply voltage	12	58	62	V
GVDD_X	Supply for logic regulators and gate-drive circuitry		DC supply voltage	10.8	12	13.2	V
VDD	Digital regulator supply voltage		DC supply voltage	10.8	12	13.2	V
R_L	Load impedance	BTL	Output filter: L = 15 uH, 0.68 µF	5	8		Ω
		PBTL		3	4		
		SE		3	4		
L_{OUTPUT}	Output filter inductance		Minimum inductance at overcurrent limit, including inductor tolerance, temperature and possible inductor saturation	7	15		µH
f_{PWM}	PWM frame rate			352	384	500	kHz
C_{PVDD}	PVDD close decoupling capacitors			0.44	1		µF
C_START	Startup ramp capacitor		BTL and PBTL configuration		330		nF
			SE and 1xBTL + 2xSE configuration		1		µF
R_{OC}	Over-current programming resistor, Resistor tolerance = 5%			24	27	33	kΩ
$R_{OC_LATCHED}$	Over-current programming resistor, Resistor tolerance = 5%			47	56	62	kΩ
T_J	Junction temperature			0		125	°C

7.4 Thermal Information

THERMAL METRIC[(1)]		TAS5634 DDV (HTSSOP) 44 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	2.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	0.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	2.0	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	1.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

Copyright © 2017, Texas Instruments Incorporated

7.5 Audio Specification Stereo (BTL)

Audio performance is recorded as a chipset consisting of a TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%) and a TAS5634 power stage with PCB and system configurations in accordance with recommended guidelines. Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 6 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_O	Power output per channel	R_L = 8 Ω, 10% THD+N		230		W
		R_L = 6 Ω, 10% THD+N Tc = 25°C		300		
		R_L = 6 Ω, 10% THD+N		295		
		R_L = 8 Ω, 1% THD+N		180		
		R_L = 6 Ω, 1% THD+N		240		
THD+N	Total harmonic distortion + noise	1 W, 1 kHz signal		0.025		%
V_n	Output integrated noise	A-weighted, AES17 measuring filter, dither off, noise shaper off(1)		215		µV
V_{OS}	Output offset voltage	No signal		50		mV
SNR	Signal-to-noise ratio(2)	A-weighted, AES17 measuring filter, noise shaper off		105		dB
DNR	Dynamic range	A-weighted, –60 dBFS (rel 1% THD+N), noise shaper on		102		dB
P_{idle}	Power dissipation due to Idle losses (IPVDD_X)	P_O = 0, channels switching(3)		8.6		W

(1) It is recommended to turn off PWM processor noise shaper while no audio present for lowest output noise
(2) SNR is calculated relative to 1% THD-N output level.
(3) Actual system idle losses also are affected by core losses of output inductors.

7.6 Audio Specifications Mono (PBTL)

Audio performance is recorded as a chipset consisting of a TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%) and a TAS5634 power stage with PCB and system configurations in accordance with recommended guidelines. Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 3 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, C_{DCB} = 470 µF, unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_O	Power output per channel	R_L = 4 Ω, 10% THD+N		460		W
		R_L = 3 Ω, 10% THD+N		590		
		R_L = 3 Ω, 10% THD+N, PVDD = 58.5V		600		
		R_L = 4 Ω, 1% THD+N		365		
		R_L = 3 Ω, 1% THD+N		465		
THD+N	Total harmonic distortion + noise	1 W, 1 kHz signal		0.04		%
V_n	Output integrated noise	A-weighted, AES17 measuring filter, dither off, noise shaper off (1)		214		µV
V_{OS}	Output offset voltage	No signal		50		mV
SNR	Signal-to-noise ratio(2)	A-weighted, AES17 measuring filter, noise shaper off		105		dB
DNR	Dynamic range	A-weighted, -60dBFS (rel 1% THD+N), noise shaper on		102		dB
P_{idle}	Power dissipation due to Idle losses (IPVDD_X)	P_O = 0, channels switching(3)		8.6		W

(1) It is recommended to turn off PWM processor noise shaper while no audio present for lowest output noise
(2) SNR is calculated relative to 1% THD-N output level.
(3) Actual system idle losses also are affected by core losses of output inductors.

Copyright © 2017, Texas Instruments Incorporated

7.7 Audio Specification 4 Channels (SE)

Audio performance is recorded as a chipset consisting of a TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%) and a TAS5634 power stage with PCB and system configurations in accordance with recommended guidelines. Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 3 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, C_{DCB} = 470 µF, unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_O	Power output per channel	R_L = 4 Ω, 10% THD+N		110		W
		R_L = 3 Ω, 10% THD+N Tc = 25°C		150		
		R_L = 3 Ω, 10% THD+N		145		
		R_L = 4 Ω, 1% THD+N		90		
		R_L = 3 Ω, 1% THD+N		115		
THD+N	Total harmonic distortion + noise	1 W, 1 kHz signal		0.05		%
V_n	Output integrated noise	A-weighted, AES17 measuring filter, dither off, noise shaper off(1)		145		µV
SNR	Signal-to-noise ratio(2)	A-weighted, AES17 measuring filter, noise shaper off		102		dB
DNR	Dynamic range	A-weighted, –60 dBFS (rel 1% THD+N), noise shaper on		102		dB
P_{idle}	Power dissipation due to Idle losses (IPVDD_X)	P_O = 0, channels switching(3)		8.6		W

(1) It is recommended to turn off PWM processor noise shaper while no audio present for lowest output noise
(2) SNR is calculated relative to 1% THD-N output level.
(3) Actual system idle losses also are affected by core losses of output inductors.

Copyright © 2017, Texas Instruments Incorporated

7.8 Electrical Characteristics

PVDD_X = 58 V, GVDD_X = 12 V, VDD = 12 V, T_C (Case temperature) = 75°C, f_S = 384 kHz, unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
INTERNAL VOLTAGE REGULATOR AND CURRENT CONSUMPTION						
DVDD	Voltage regulator, only used as a reference node	VDD = 12 V	3.0	3.3	3.6	V
AVDD	Voltage regulator, only used as a reference node	VDD = 12 V		7.8		V
I_{VDD}	VDD supply current	Operating, 50% duty cycle		23		mA
		Idle, reset mode		23		
I_{GVDD_X}	Gate-supply current per full-bridge	50% duty cycle		22		mA
		Reset mode		3		
I_{PVDD_X}	Full-bridge idle current	50% duty cycle without load		148		mA
		$\overline{\text{RESET}}$ low		3.5		
OUTPUT-STAGE MOSFETs						
$R_{DS(on),\ LS}$	Drain-to-source resistance, low side (LS)	T_J = 25°C, excludes metallization resistance, GVDD = 12 V		80		mΩ
$R_{DS(on),\ HS}$	Drain-to-source resistance, high side (HS)			80		mΩ
I/O PROTECTION						
$V_{uvp,GVDD}$	Undervoltage protection limit, GVDD_X			8.5		V
$V_{uvp,GVDD,\ hyst}$ (1)				0.7		V
$V_{uvp,VDD}$	Undervoltage protection limit, VDD			8.5		V
$V_{uvp,VDD,\ hyst}$ (1)				0.7		V
$V_{uvp,PVDD}$	Undervoltage protection limit, PVDD_X			8.5		V
$V_{uvp,PVDD,hyst}$ (1)				0.7		V
OTW (1)	Overtemperature warning		115	125	135	°C
OTW_{hyst} (1)	Temperature drop needed below OTW temperature for $\overline{\text{OTW}}$ to be inactive after $\overline{\text{OTW}}$ event.			20		°C
OTE (1)	Overtemperature error		145	155	165	°C
$OTE\text{-}OTW_{differential}$ (1)	OTE-OTW differential			30		°C
OTE_{HYST} (1)	A device reset is needed to clear $\overline{\text{FAULT}}$ after an OTE event			20		°C
OLPC	Overload protection counter	f_{PWM} = 384 kHz		2.6		ms
I_{OC}	Overcurrent limit protection	Resistor – programmable, nominal peak current in 1Ω load, ROC = 27 kΩ (Typ)		14		A
$I_{OC_LATCHED}$	Overcurrent limit protection, latched	Resistor – programmable, nominal peak current in 1Ω load, ROC = 56 kΩ (Typ)		14		A
I_{DC_OC}	Speaker DC protection limit	Resistor – programmable, ROC = 27 kΩ		1.5		A
$I_{DC_OC_LATCHED}$	Speaker DC protection limit	Resistor – programmable, ROC = 56 kΩ		1.5		A
I_{OCT}	Overcurrent response time	Time from application of short condition to Hi-Z of affected half bridge		150		ns
I_{PD}	Internal pulldown resistor at output of each half bridge	Connected when $\overline{\text{RESET}}$ is active to provide bootstrap charge. Not used in SE mode.		3		mA
STATIC DIGITAL SPECIFICATIONS						
V_{IH}	High level input voltage	INPUT_X, M1, M2, M3, $\overline{\text{RESET}}$	1.9			V
V_{IL}	Low level input voltage				0.8	V
LEAKAGE	Input leakage current				100	μA
OTW / SHUTDOWN (FAULT)						
R_{INT_PU}	Internal pullup resistance, $\overline{\text{OTW}}$, $\overline{\text{CLIP}}$, $\overline{\text{FAULT}}$ to DVDD		20	26	33	kΩ
V_{OH}	High level output voltage	Internal pullup resistor	3	3.3	3.6	V
V_{OL}	Low level output voltage	I_O = 4mA		200	500	mV
FANOUT	Device fanout $\overline{\text{OTW}}$, $\overline{\text{FAULT}}$, $\overline{\text{CLIP}}$	No external pullup		30		devices

(1) Specified by design.

Copyright © 2017, Texas Instruments Incorporated

7.9 Typical Characteristics

7.9.1 BTL Configuration

Measurement Conditions: TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%), Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 6 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, 20 Hz to 20 kHz BW (AES17 low pass filter), unless otherwise noted.

图 1. Total Harmonic Distortion + Noise vs Output Power

图 2. Output Power vs Supply Voltage

图 3. Total Harmonic Distortion + Noise vs Frequency

图 4. Output Power vs Supply Voltage

版权 © 2017, Texas Instruments Incorporated

BTL Configuration (接下页)

图 5. Efficiency vs 2 Channel Output Power

图 6. Power Loss vs 2 Channel Output Power

图 7. Output Power vs Case Temperature

图 8. Noise Amplitude vs Frequency

7.9.2 PBTL Configuration

Measurement Conditions: TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%), Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 3 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, C_{DCB} = 470 µF, 20 Hz to 20 kHz BW (AES17 low pass filter), unless otherwise noted.

图 9. Total Harmonic Distortion + Noise vs Output Power

图 10. Output Power vs Supply Voltage

图 11. Total Harmonic Distortion + Noise vs Frequency

图 12. Output Power vs Supply Voltage

图 13. Output Power vs Case Temperature

版权 © 2017, Texas Instruments Incorporated

7.9.3 SE Configuration

Measurement Conditions: TAS5548 PWM Processor (AD-mode, modulation index limited to 97.7%), Audio frequency = 1 kHz, PVDD_X = 58 V, GVDD_X = 12 V, R_L = 3 Ω, f_S = 384 kHz, R_{OC} = 30 kΩ, T_C = 75°C, Output Filter: L_{DEM} = 15 µH, C_{DEM} = 680 nF, C_{DCB} = 470 µF, 20 Hz to 20 kHz BW (AES17 low pass filter), unless otherwise noted.

图 14. Total Harmonic Distortion + Noise vs Output Power

图 15. Output Power vs Supply Voltage

图 16. Total Harmonic Distortion + Noise vs Frequency

图 17. Output Power vs Supply Voltage

图 18. Output Power vs Case Temperature

8 Detailed Description

8.1 Overview

The TAS5634 is a PWM Input, Class-D Audio amplifier power stage that can be paired with TI digital-input PWM modulator like the TAS5548 or TAS5558. The TAS5634 supports up to 58V on the output stage power supply (PVDD) to deliver up to 2 x 300 W (6Ω) or 1 x 600 W (3Ω) for higher impedance loads. The output of the TAS5634 can be configured in single-ended (SE), bridge-tied load (BTL) or parallel bridge-tied load (PBTL) output, which supports 4-channels, stereo, or mono, respectively. It requires two power supply rails for operation, PVDD for the output power stage and 12 V for the gate drive (GVDD) and internal circuitry (VDD). 图 19 shows typical connections for BTL outputs. A detailed schematic can be viewed in TAS5634EVM User's Guide.

版权 © 2017, Texas Instruments Incorporated

8.2 Functional Block Diagrams

(1) Logic AND is inside or outside the micro processor.

图 19. Typical System Block Diagram

Functional Block Diagrams (接下页)

图 20. Functional Block Diagram

版权 © 2017, Texas Instruments Incorporated

8.3 Feature Description

8.3.1 Closed-Loop Architecture

The TAS5634 is designed with closed-loop feedback to reduce noise and eliminate distortion caused by the power supply and output stage FETs. The integrated closed-loop architecture makes it simple and easy to convert from an audio digital source directly to power delivery in one step while maintaining great performance.

8.3.2 Power Supplies

The TAS5634 requires only two supplies for normal operation including a high-voltage output stage supply, PVDD, and a lower voltage 12V voltage supply for gate drive and low-voltage analog and digital circuits. Two internal regulators provide voltage regulation for the digital (DVDD) and analog (AVDD) circuit using the 12V VDD voltage supply. Additionally, an integrated bootstrap (floating) supply provides the necessary voltage for the high-side MOSFETs for each half-bridge.

To provide the best electrical and acoustical characteristics, the PWM signal path including gate drive and output stage are designed as identical, independent half-bridges. For this reason, each half-bridge has separate bootstrap pins (BST_X) and each full-bridge has separate power stage supply (PVDD_X) and gate supply (GVDD_X) pins.

Special attention should be paid to the power-stage power supply; this includes component selection, PCB placement, and routing. As indicated, each full-bridge has independent power-stage supply pins (PVDD_X). For optimal electrical performance, EMI compliance, and system reliability, it is important that each PVDD_X connection is decoupled with a minimum of 470 nF ceramic capacitance and placed as close as possible to each supply pin. It is recommended to follow the PCB layout of the TAS5634 reference design. For additional information on recommended power supply and required components, see the application diagrams in this data sheet.

The power-supply sequence is not critical because of the internal power-on-reset circuit. The TAS5634 is fully protected against erroneous power-stage turn on due to parasitic gate charging when power supplies are applied. Thus, voltage-supply ramp rates (dV/dt) are non-critical within the specified range (see the Recommended Operating Conditions table of this data sheet).

8.3.2.1 BST, Bootstrap Supply

The TAS5634 uses bootstrap circuits to properly turn on the high-side MOSFETs. A small ceramic capacitor must be connected from each bootstrap pin (BST_X) to the power-stage output pin (OUT_X). When the power-stage output is low, the bootstrap capacitor is charged through an internal diode connected between the gate-drive power-supply pin (GVDD_X) and the bootstrap pin (BST_X). When the power-stage output is high, the bootstrap capacitor potential is shifted above the output potential and thus provides a suitable voltage supply for the high-side gate driver. In an application with PWM switching frequencies in the range from 352kHz to 500 kHz, it is recommended to use 33 nF ceramic capacitors, size 0603 or 0805, for the bootstrap supply. These 33-nF capacitors ensure sufficient energy storage, even during minimal PWM duty cycles, to keep the high-side power stage MOSFETs fully turned on during the remaining part of the PWM cycle.

8.3.2.2 PVDD, Output Stage Power Supply

The PVDD_x voltage pins supply the high voltage and current needed for driving the speaker load.

1. Place at least 1 μF decoupling capacitance as close as possible to each supply pin, PVDD_AB and PVDD_CD. TI recommends to use ceramic capacitors, which have low series resistance (ESR). The decoupling capacitors provide current each output stage switch cycle.
2. Add a minimum of 470 μF bulk capacitance to each PVDD_x pin. More capacitance may be required if the power supply has low bandwidth or does not respond quickly to transients.
3. Minimize trace lengths between decoupling and bulk capacitance to reduce inductance between the TAS5634 and the supply capacitors.

8.3.2.3 GVDD, Gate-Drive Power Supply

The GVDD_x, 12 V power supply is required for the gate-drive section of the TAS5634. Place a minimum of 100 nF decoupling capacitor near each GVDD_x pin. For best audio performance, place a total of 10 μF bulk capacitance on the 12V power supply.

Feature Description (接下页)

8.3.2.4 VDD Supply, Internal Regulators (DVDD and AVDD)

The TAS5634 has two internal regulators, which are used to power the low voltage digital (DVDD) and analog (AVDD) circuitry. The 12V VDD pin can be supplied from the same power supply as GVDD_x. For best audio performance, separate VDD from GVDD_AB and GVDD_CD using RC filters. The RC filters will provide high-frequency isolation and minimize the amount of switching noise on DVDD and AVDD.

8.3.3 System Power-Up / Power-Down Sequence

8.3.3.1 Powering Up

The TAS5634 does not require a power-up sequence. The outputs of the H-bridges remain in a high-impedance state until the gate-drive supply voltage (GVDD_X) and VDD voltage are above the undervoltage protection (UVP) voltage threshold (see the Electrical Characteristics table of this data sheet). Although not specifically required, it is recommended to hold RESET in a low state while powering up the device. This allows an internal circuit to charge the external bootstrap capacitors by enabling a weak pulldown of the half-bridge output.

8.3.3.2 Powering Down

The TAS5634 does not require a power-down sequence. The device remains fully operational as long as the gate-drive supply (GVDD_X) voltage and VDD voltage are above the undervoltage protection (UVP) voltage threshold (see the Electrical Characteristics table of this data sheet). Although not specifically required, it is a good practice to hold RESET low during power down, thus preventing audible artifacts including pops or clicks.

8.3.4 Startup and Shutdown Ramp Sequence (C_START)

The integrated startup and stop sequence ensures a click and pop free startup and shutdown sequence of the amplifier. The startup sequence uses a voltage ramp with a duration set by the CSTART capacitor. The sequence uses the input PWM signals to generate output PWM signals, hence input idle PWM should be present during both startup and shut down ramping sequences.

VDD, GVDD_X and PVDD_X power supplies must be turned on and with settled outputs before starting the startup ramp by setting RESET high.

During startup and shutdown ramp the input PWM signals should be in muted condition with the PWM processor noise shaper activity turned off (50% duty cycle).

The duration of the startup and shutdown ramp is 100 ms + X ms, where X is the CSTART capacitor value in nF. It is recommended to use 330 nF CSTART in BTL and PBTL mode and 1 µF in SE mode configuration. This results in ramp times of 430 ms and 1.1 s respectively. The longer ramp time in SE configuration allows charge and discharge of the output AC coupling capacitor without audible artifacts. See the Table 1 Mode Selection Pins for a complete list of recommended C_START values.

版权 © 2017, Texas Instruments Incorporated

Feature Description (接下页)

图 21. Start-Up and Shutdown Ramp

8.3.5 Device Protection System

The TAS5634 contains advanced protection circuitry carefully designed to facilitate system integration and ease of use, as well as to safeguard the device from permanent failure due to a wide range of fault conditions such as short circuits, overload, overtemperature, and undervoltage. The TAS5634 responds to a fault by immediately setting the power stage in a high-impedance (Hi-Z) state and asserting the $\overline{\text{FAULT}}$ pin low. In situations other than overload and overtemperature error (OTE), the device automatically recovers when the fault condition has been removed, i.e., the supply voltage has increased.

The device will function on errors, as shown in the following table.

表 2. Device Protection

BTL Mode		SE Mode	
Channel Fault	**Turns Off**	**Channel Fault**	**Turns Off**
A	A+B	A	A+B
B		B	
C	C+D	C	C+D
D		D	

Bootstrap UVP does not shutdown according to the table, it shuts down the respective high-side FET.

8.3.6 Overload and Short Circuit Current Protection

TAS5634 has fast reacting current sensors with a programmable trip threshold (OC threshold) on all high-side and low-side FETs. To prevent output current to increase beyond the programmed threshold, TAS5634 has the option of either limiting the output current for each switching cycle (Cycle By Cycle Current Control, CB3C) or to perform an immediate shutdown of the output in case of excess output current (Latching Shutdown). CB3C prevents premature shutdown due to high output current transients caused by high level music transients and a drop of real speaker's load impedance, and will allow the output current to be limited to a maximum programmed level. If the maximum output current persists, i.e. the power stage being overloaded with too low load impedance, the device will shut down the affected output channel and the affected output will be put in a high-impedance (Hi-Z) state until a /RESET cycle is initiated. CB3C works individually for each half bridge output. If an over current event is triggered, CB3C will perform a state flip of the half bridge output that will be cleared upon beginning of next PWM frame.

图 22. CB3C Timing Example

During CB3C an over load counter will increment for each over current event and decrease for each non-over current PWM cycle. This allows full amplitude transients into a low speaker impedance without a shutdown protection action. In case of a short circuit condition, the over current protection will limit the output current by the CB3C operation and eventually shut down the affected output if the overload counter reaches its maximum value. If a latched OC operation is required such that the device will shut down the affected output immediately upon first detected over current event, this protection mode should be selected.

The over current threshold and mode (CB3C or Latched OC) is programmed by the OC_ADJ resistor value. The OC_ADJ resistor needs to be within its intentional value range for either CB3C operation or Latched OC operation.

图 23. OC Threshold versus OC_ADJ Resistor Value Example

版权 © 2017, Texas Instruments Incorporated

表 3. OC_ADJ Resistor Value for OC Threshold

OC_ADJ Resistor Value	Protection Mode	OC Threshold
24 kΩ	CB3C	15.5 A
27 kΩ (Typ)	CB3C	14 A
30 kΩ	CB3C	13 A
33 kΩ	CB3C	12 A
47 kΩ	Latched OC	15.5 A
56 kΩ (Typ)	Latched OC	14 A
68 kΩ	Latched OC	13 A
62 kΩ	Latched OC	12 A

TI recommends to use a 27kΩ (CB3C) or 56kΩ (Latched) overcurrent adjust resistor value for typical applications. When using 24 kΩ (CB3C) or 47 kΩ (Latched) OC_ADJ resistor values, layout is critical for device reliability due to increased current during overcurrent events. Please carefully follow the guidelines in section Printed Circuit Board Requirements and only use these resistor values if required to deliver the desired power to the load.

8.3.7 DC Speaker Protection

The output DC protection scheme protects a connected speaker from excess DC current caused by a speaker wire accidentally shorted to chassis ground. Such short circuit would result in a DC voltage of PVDD/2 across the speaker, which potentially can result in destructive current levels. The output DC protection detects any unbalance of the output and input current of a BTL output, and in case of the unbalance exceeding a programmed threshold, the overload counter will increment until its maximum value and the affected output channel will be shut down. Output DC protection is designed for use in BTL configuration with AD mode modulation, and should be disabled if BD mode operation is used due to the output filter inductors' ripple currents being in phase in BD mode and will thus be counted as an unbalanced current. DC Speaker Protection can be disabled for BTL operation with BD mode modulation, see Mode Setup Table for configuration.

8.3.8 Pin-To-Pin Short Circuit Protection (PPSC)

The PPSC detection system protects the device from permanent damage if a power output pin (OUT_X) is shorted to GND or PVDD_X. For comparison, the OC protection system detects an over current after the demodulation filter where PPSC detects shorts directly at the pin before the filter. PPSC detection is performed at startup i.e. when VDD is supplied, consequently a short to either GND or PVDD_X after system startup will not activate the PPSC detection system. When PPSC detection is activated by a short on the output, all half bridges are kept in a Hi-Z state until the short is removed, the device then continues the startup sequence and starts switching. The detection is controlled globally by a two step sequence. The first step ensures that there are no shorts from OUT_X to GND, the second step tests that there are no shorts from OUT_X to PVDD_X. The total duration of this process is roughly proportional to the capacitance of the output LC filter. The typical duration is <15 ms/μF. While the PPSC detection is in progress, $\overline{\text{FAULT}}$ is kept low, and the device will not react to changes applied to the $\overline{\text{RESET}}$ pins. If no shorts are present the PPSC detection passes, and $\overline{\text{FAULT}}$ is released. A device reset will not start a new PPSC detection. PPSC detection is enabled in BTL output configuration, the detection is not performed in SE mode. To make sure not to trip the PPSC detection system it is recommended not to insert resistive load to GND or PVDD_X.

8.3.9 Overtemperature Protection

The TAS5634 has a two-level temperature-protection system that asserts an active-low warning signal ($\overline{\text{OTW}}$) when the device junction temperature exceeds 125°C (typical). If the device junction temperature exceeds 155°C (typical), the device is put into thermal shutdown, resulting in all half-bridge outputs being set in the high-impedance (Hi-Z) state and $\overline{\text{FAULT}}$ being asserted low. OTE is latched in this case. To clear the OTE latch, $\overline{\text{RESET}}$ must be asserted. Thereafter, the device resumes normal operation.

8.3.10 Overtemperature Warning, $\overline{\text{OTW}}$

The over temperature warning $\overline{\text{OTW}}$ asserts when the junction temperature has exceeded recommended operating temperature. Operation at junction temperatures above $\overline{\text{OTW}}$ threshold is exceeding recommended operation conditions and is strongly advised to avoid.

If $\overline{\text{OTW}}$ asserts, action should be taken to reduce power dissipation to allow junction temperature to decrease until it gets below the $\overline{\text{OTW}}$ hysteresis threshold. This action can be decreasing audio volume or turning on a system cooling fan.

8.3.11 Undervoltage Protection (UVP) and Power-On Reset (POR)

The UVP and POR circuits of the TAS5634 fully protect the device in any power-up/down and brownout situation. While powering up, the POR circuit resets the overload circuit (OLP) and ensures that all circuits are fully operational when the GVDD_X and VDD supply voltages reach stated in the Electrical Characteristics table. Although GVDD_X and VDD are independently monitored, a supply voltage drop below the UVP threshold on any VDD or GVDD_X pin results in all half-bridge outputs immediately being set in the high-impedance (Hi-Z) state and $\overline{\text{FAULT}}$ being asserted low. The device automatically resumes operation when all supply voltages have increased above the UVP threshold.

8.3.12 Error Reporting

Note that asserting $\overline{\text{RESET}}$ low forces the $\overline{\text{FAULT}}$ signal high, independent of faults being present. TI recommends monitoring the $\overline{\text{OTW}}$ signal using the system micro controller and responding to an overtemperature warning signal by, e.g., turning down the volume to prevent further heating of the device resulting in device shutdown (OTE).

To reduce external component count, an internal pullup resistor to 3.3 V is provided on $\overline{\text{FAULT}}$, $\overline{\text{CLIP}}$, and $\overline{\text{OTW}}$ outputs. See Electrical Characteristics table for actual values.

The $\overline{\text{FAULT}}$, $\overline{\text{OTW}}$, pins are active-low, open-drain outputs. Their function is for protection-mode signaling to a PWM controller or other system-control device.

Any fault resulting in device shutdown is signaled by the $\overline{\text{FAULT}}$ pin going low. Likewise, $\overline{\text{OTW}}$ goes low when the device junction temperature exceeds 125°C (see 表 4).

表 4. Error Reporting

$\overline{\text{FAULT}}$	$\overline{\text{OTW}}$	DESCRIPTION
0	0	Overtemperature (OTE) or overload (OLP) or undervoltage (UVP)
0	1	Overload (OLP) or undervoltage (UVP)
1	0	Junction temperature higher than 125°C (overtemperature warning)
1	1	Junction temperature lower than 125°C and no OLP or UVP faults (normal operation)

版权 © 2017, Texas Instruments Incorporated

8.3.13 Fault Handling

If a fault situation occurs while in operation, the device will act accordingly to the fault being a global or a channel fault. A global fault is a chip-wide fault situation and will cause all PWM activity of the device to be shut down, and will assert $\overline{\text{FAULT}}$ low. A global fault is a latching fault and clearing $\overline{\text{FAULT}}$ and restart operation requires resetting the device by toggling $\overline{\text{RESET}}$. Toggling $\overline{\text{RESET}}$ should never be allowed with excessive system temperature, so it is advised to monitor $\overline{\text{RESET}}$ by a system microcontroller and only allow releasing $\overline{\text{RESET}}$ ($\overline{\text{RESET}}$ high) if the $\overline{\text{OTW}}$ signal is cleared (high). A channel fault will result in shutdown of the PWM activity of the affected channel(s). Note that asserting $\overline{\text{RESET}}$ low forces the $\overline{\text{FAULT}}$ signal high, independent of faults being present. TI recommends monitoring the $\overline{\text{OTW}}$ signal using the system micro controller and responding to an over temperature warning signal by, that is, turning down the volume to prevent further heating of the device resulting in device shutdown (OTE).

表 5. Fault Handling

Fault/Event	Fault/Event Description	Global or Channel	Reporting Method	Latched/Self Clearing	Action needed to Clear	Output FETs
PVDD_X UVP	Voltage Fault	Global	$\overline{\text{FAULT}}$ Pin	Self Clearing	Increase affected supply voltage	Hi-Z
VDD UVP						
GVDD_X UVP						
AVDD UVP						
POR (DVDD UVP)	Power On Reset	Global	$\overline{\text{FAULT}}$ Pin	Self Clearing	Allow DVDD to rise	H-Z
BST UVP	Voltage Fault	Channel (half bridge)	None	Self Clearing	Allow BST cap to recharge (lowside on, VDD 12V)	High-side Off
OTW	Thermal Warning	Global	$\overline{\text{OTW}}$ Pin	Self Clearing	Cool below lower OTW threshold	Normal operation
OTE (OTSD)	Thermal Shutdown	Global	$\overline{\text{FAULT}}$ Pin	Latched	Toggle $\overline{\text{RESET}}$	Hi-Z
OLP (CB3C >2.6 ms)	OC shutdown	Channel	$\overline{\text{FAULT}}$ Pin	Latched	Toggle $\overline{\text{RESET}}$	Hi-Z
Latched OC (ROC > 47 k)	OC shutdown	Channel	$\overline{\text{FAULT}}$ Pin	Latched	Toggle $\overline{\text{RESET}}$	Hi-Z
CB3C (24k < ROC < 33k)	OC Limiting	Channel	None	Self Clearing	Reduce signal level or remove short	Flip state, cycle by cycle at fs/2
Stuck at Fault(1) (1 to 3 channels)	No PWM	Channel	None	Self Clearing	Resume PWM	Hi-Z
Stuck at Fault(1) (All channels)	No PWM	Global	None	Self Clearing	Resume PWM	Hi-Z

(1) Stuck at Fault occurs when input PWM drops below minimum PWM frame rate given in the *Recommended Operating Conditions* table of this data sheet.

8.3.14 System Design Consideration

A rising-edge transition on $\overline{\text{RESET}}$ input allows the device to execute the startup sequence and starts switching.

Apply audio only according to the timing information for startup and shutdown sequence. That will start and stop the amplifier without audible artifacts in the output transducers.

The $\overline{\text{CLIP}}$ signal indicates that the output is approaching clipping (when output PWM starts skipping pulses due to loop filter saturation). The signal can be used to initiate an audio volume decrease or to adjust the power supply rail.

The device inverts the audio signal from input to output.

The DVDD and AVDD pins are not recommended to be used as a voltage source for external circuitry.

8.4 Device Functional Modes

There are three main output modes supported on the TAS5634 including stereo BTL mode, mono PBTL mode and 4-channel single-ended mode. In addition, a combination of one BTL channel and two SE channels for a 2.1 system can also be selected. The device supports two PWM modulation modes, AD and BD. AD modulation mode supports single-ended (SE) or differential PWM inputs. AD modulation can also be configured to have SE, BTL, BTL + SE, or PBTL outputs. BD modulation requires differential PWM inputs. BD modulation can only be configured in BTL or PBTL mode.

图 24. Device Functional Modes Configurations

8.4.1 Stereo, Bridge-tied Load (BTL)

In bridge-tied load (BTL) mode, the device operates as a 2-channel, stereo amplifier. BTL uses two of the output stage half-bridges to product up to twice PVDD across the load. BTL mode has a few configuration options:

- AD or BD Modulation
- Single-ended (AD) or Differential Input (AD or BD)
- DC Speaker Protection in AD modulation mode

When using the singled-ended input configuration, the input signal is converted to a differential signal to drive the output stage of the TAS5634.

See Table 1. Mode Selection Pins for the appropriate pin configurations and section Typical BTL Application for specific application setup information.

8.4.2 Mono, Paralleled Bridge-tied Load (PBTL)

In parallel bridge-tied load (PBTL) mode, the device operates as a 1-channel, mono amplifier. PBTL is typically used for 3 Ω and 4 Ω impedances delivering up to twice the current compared with the BTL configuration. PBTL configuration options include:

- AD or BD Modulation
- Single-ended (AD) or Differential Input (AD or BD)
- DC Speaker Protection in AD modulation mode

版权 © 2017, Texas Instruments Incorporated

Device Functional Modes (接下页)

When using the single-ended input configuration, the single-ended input signal is converted to a differential signal to drive the output stage of the TAS5634.

See Table 1. Mode Selection Pins for the appropriate pin configurations and section Typical PBTL Application for specific application setup information.

8.4.3 4-Channel, Single-ended (SE)

In single-ended (SE) mode, the device operates as a 4-channel amplifier. Each output, OUT_A, OUT_B, OUT_C and OUT_D act as independent channels. Single-ended mode only supports AD mode and single-ended input. See Table 1. Mode Selection Pins for the appropriate pin configurations and section Typical SE Application for specific application setup information.

8.4.4 BD Modulation

The TAS5634 supports BD mode modulation. See table Mode Selection Pins to configure the device mode pins for BD mode modulation. BD mode requires a PWM modulator, like the TAS5548, to provide two BD modulated PWM signals to the inputs of the TAS5634. Note that DC Speaker Protection is disabled in BD mode operation.

Figure 25 shows example BD modulation waveforms at idle, positive output, and negative output.

图 25. BD Modulation Switching Waveforms

8.4.5 Device Reset

When $\overline{\text{RESET}}$ is asserted low, all power-stage FETs in the four half-bridges are forced into a high-impedance (Hi-Z) state.

Device Functional Modes (接下页)

In BTL modes, to accommodate bootstrap charging prior to switching start, asserting the reset input low enables weak pulldown of the half-bridge outputs. In the SE mode, the output is forced into a high impedance state when asserting the reset input low. Asserting reset input low removes any fault information to be signaled on the $\overline{\text{FAULT}}$ output, i.e., $\overline{\text{FAULT}}$ is forced high. A rising-edge transition on reset input allows the device to resume operation after an overload fault. To ensure thermal reliability, the rising edge of $\overline{\text{RESET}}$ must occur no sooner than 4 ms after the falling edge of $\overline{\text{FAULT}}$.

8.4.6 Unused Output Channels

If any output channels are unused, it is recommended to disable switching of unused output nodes to reduce power consumption. Furthermore by disabling unused output channels the cost of unused output LC demodulation filters can be avoided.

Disable a channel by leaving the bootstrap capacitor (BST) unpopulated and connecting the respective input to GND. The unused output pin(s) can be left floating. Please note that the PVDD decoupling capacitors still need to be populated.

表 6. Unused Output Channels

Operating Mode	PWM Input	Output Configuration	Unused Channel	INPUT_A	INPUT_B	INPUT_C	INPUT_D	Unpopulated Component(s)
000	2N	2 x BTL	AB CD	GND PWMa	GND PWMb	PWMc GND	PWMd GND	BST_A & BST_B capacitor BST_C & BST_D capacitor
001	1N							
010	2N							
101	1N	4 x SE	A	GND	PWMb	PWMc	PWMd	BST_A capacitor
			B	PWMa	GND	PWMc	PWMd	BST_B capacitor
			C	PWMa	PWMb	GND	PWMd	BST_C capacitor
			D	PWMa	PWMb	PWMc	GND	BST_D capacitor

版权 © 2017, Texas Instruments Incorporated

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

These typical connection diagrams highlight the required external components and system level connections for proper operation of the device in several common use cases. Each of these configurations can be tested using the TAS5634EVM. Please contact TI through TI.com or by visiting the TI E2E Forum at www.e2e.ti.com for design assistance and join the audio amplifier discussion forum for additional information.

9.2 Typical Applications

9.2.1 Typical BTL Application

See 图 26 for application schematic. In this application, differential PWM inputs are used with AD modulation from the PWM modulator (TAS5558). AD modulation scheme is defined as PWM(+) as opposite polarity from PWM(–).

图 26. Typical Differential (2N) BTL Application

Typical Applications (接下页)

9.2.1.1 Design Requirements

For this design example, us the values shown in 表 7.

表 7. BTL Design Requirements

PARAMETERS	VALUES
PVDD Supply Voltage	12 V to 58 V
GVDD and VDD Voltage	12 V
Device Configuration	AD Modulation, Differential Input
Mode Pins	M3 = GND, M2 = GND, M1 = GND
INPUT_A	PWM_1+
INPUT_B	PWM_1-
INPUT_C	PWM_2+
INPUT_D	PWM_2-
PWM modulator	TAS5548
Output filters	Inductor: 15 μH, Capacitor: 0.68 μF
Speaker	6 Ω minimum
C_START Capacitor	330 nF
OC_ADJ Resistor	27 kΩ (14 A per channel, Cycle-by-cycle Current Limit)

9.2.1.2 Detailed Design Procedure

- Follow the recommended component placement, layout and routing guidelines shown in the Layout Example section.
- The most critical section of the circuit is the power supply pins, the amplifier output signals and the high frequency signals.
- For specific application questions and support go to the TI E2E Forum at www.e2e.ti.com.

9.2.1.3 Pin Connections

- Pin 1 - GVDD_AB - The gate-drive voltage for half-bridges A and B. Place a 0.1-μF decoupling capacitor placed near the pin.
- Pin 2 - VDD - The supply pin for internal voltage regulators AVDD and DVDD. Place a 10-μF bulk capacitor and a 0.1-μF decoupling capacitor near the pin.
- Pin 3 - R_{OC} - Programming resistor for the overcurrent (OC) threshold. Place a resistor to ground. See table OC_ADJ Resistor Value for OC Threshold for the appropriate resistor value.
- Pin 4 - $\overline{\text{RESET}}$ - Device reset. When asserted, output stage is Hi-Z and there is no PWM switching. This pin can be controlled by a switch, microcontroller or processor.
- Pins 5 and 6 - INPUT_A and INPUT_B - Differential PWM input pair for A and B BTL channel with signals provided by a PWM modulator such as the TAS5548.
- Pin 7 - C_START - Start-up ramp capacitor must be 330nf for BTL/PBTL or 1 μF for SE configuration.
- Pin 8 - DVDD - Digital output supply pin is connected to 1-μF decoupling capacitor
- Pins 9-12 - GND - Connect to board GND.
- Pin 13 - AVDD - Analog output supply pin. Connect a 1-μF decoupling capacitor to device GND, pins 9-12.
- Pins 14 and 15 - INPUT_C and INPUT_D - Differential PWM input pair for C and D BTL channel with signals provided by a PWM modulator such as the TAS5548.
- Pin 16 - $\overline{\text{FAULT}}$ - Fault pin can be monitored by a microcontroller through GPIO pin. System can decide to assert reset or shutdown.
- Pin 17 - $\overline{\text{OTW}}$ - Overtemperature warning pin can be monitored by a microcontroller through a GPIO pin. System can decide to turn on fan or lower output power.
- Pin 18 - $\overline{\text{CLIP}}$ - Output clip indicator can be monitored by a microcontroller through a GPIO pin. System can decide to lower the volume.
- Pins 19-21 - M1, M2, M3 - Mode pins set the input and output configurations. For this configuration M1-M3

版权 © 2017, Texas Instruments Incorporated

are grounded. These mode pins must be hardware configured and set before starting device. Do not adjust while TAS5634 is operating.

- Pin 22 - GVDD_CD - The gate-drive voltage for half-bridges C and D. Place a 0.1-μF decoupling capacitor placed near the pin.
- Pins 23, 24, 43, 44 - BST_A, BST_B, BST_C, BST_D - Bootstrap pins for half-bridges A, B, C, and D. Connect 33 nF from this pin to corresponding output pins.
- Pins 25, 26, 33, 34, 41, 42 - GND - Connect to board ground and decoupling capacitors connected to PVDD_X.
- Pins 27, 28, 32, 35, 39, 40 - OUT_A, OUT_B, OUT_C, OUT_D - Output pins from half-bridges A, B, C, and D. Connect bootstrap capacitors and differential LC filter.
- Pins 29, 30, 31, 36, 37, 38 - PVDD_AB, PVDD_CD - Power supply pins to half-bridges A, B, C, and D. A and B form a full-bridge and C and D form another full-bridge. A 470-μF bulk capacitor is recommended for each full-bridge power pins. Place one 1-μF decoupling capacitor next to each pin.

9.2.1.4 Application Curves

图 27. Total Harmonic Distortion + Noise vs Output Power

图 28. Output Power vs Supply Voltage

9.2.2 Typical PBTL Configuration

Use the sectionDetailed Design Procedure in the Typical BTL Application section for a pin description and setup.

图 29. Typical Differential (2N) PBTL Application

表 8. PBTL Design Requirements

PARAMETERS	VALUES
PVDD Supply Voltage	12 V to 58 V
GVDD and VDD Voltage	12 V
Device Configuration	AD Modulation, Differential Input
Mode Pins	M3 = DVDD, M2 = GND, M1 = GND
INPUT_A	PWM_A+
INPUT_B	PWM_A-
INPUT_C	GND
INPUT_D	GND
PWM modulator	TAS5548
Output filters	Inductor: 15 µH, Capacitor: 0.68 µF
Speaker	3 Ω minimum
C_START Capacitor	330 nF
OC_ADJ Resistor	27 kΩ (14 A per channel, Cycle-by-cycle Current Limit)

版权 © 2017, Texas Instruments Incorporated

9.2.2.1 Application Curves

图 30. Total Harmonic Distortion + Noise vs Output Power

图 31. Output Power vs Supply Voltage

9.2.3 Typical SE Configuration

See 图 32 for application schematic. In this application, four single-ended PWM inputs are used with AD modulation from the PWM modulator such as the TAS5558. AD modulation scheme is defined as PWM(+) is opposite polarity from PWM(–), but in this case there is only a single-ended signal. The single-ended (SE) output configuration is often used to drive four independent channels in one TAS5634 device.

图 32. Typical (1N) SE Application

表 9. SE Design Requirements

PARAMETERS	VALUES
PVDD Supply Voltage	12 V to 58 V
GVDD and VDD Voltage	12 V
Device Configuration	AD Modulation, Single-Ended Input
Mode Pins	M3 = DVDD, M2 = GND, M1 = DVDD
INPUT_A	PWM_1
INPUT_B	PWM_2
INPUT_C	PWM_3
INPUT_D	PWM_4
PWM modulator	TAS5548
Output filters	Inductor: 15 µH, Capacitor: 0.68 µF
Speaker	3 Ω minimum
C_START Capacitor	1 µF
OC_ADJ Resistor	27 kΩ (14 A per channel, Cycle-by-cycle Current Limit)

版权 © 2017, Texas Instruments Incorporated

9.2.3.1 Application Curves

图 33. Total Harmonic Distortion + Noise vs Output Power

图 34. Output Power vs Supply Voltage

10 Power Supply Recommendations

10.1 Power Supplies

To simplify power supply design, the TAS5634 requires only two voltage supplies. A 12-V supply and 58-V (typical) power-stage supply. An internal voltage regulator provides the supply voltage for the digital and low-voltage analog circuitry. Additionally, a floating voltage supply, using the built-in bootstrap circuit, provides the high-side gate drive voltage for each half-bridge.

The PWM signal paths, including gate drive and output stage, are designed as identical, independent half-bridges. Each half-bridge has separate bootstrap pins (BST_X) and each full-bridge has separate power stage supply (PVDD_X) and gate supply (GVDD_X). TI highly recommends separating GVDD_AB, GVDD_CD, and VDD on the printed-circuit-board (PCB) using RC filters (see Layout Example for details). These RC filters provide the recommended high-frequency isolation between GVDD_X and VDD. Place all decoupling capacitors close to the associated pins to avoid stray inductance.

Pay special attention to the power-stage power supply; this includes component selection, PCB placement and routing. For optimal electrical performance, EMI compliance, and system reliability, it is important that each PVDD_X connection is decoupled with a minimum of 470-nF ceramic capacitors placed as close as possible to each supply pin. TI recommends following the PCB layout of the TAS5634EVM. For additional information on recommended power supply and required components, see the application diagrams in this data sheet.

The 12-V supply must have low-noise and low-output-impedance from a voltage regulator. Likewise, the 58-V power stage supply is assumed to have low output impedance and low noise. The power-supply sequence is not critical because of the internal power-on reset circuit. This makes the TAS5634 protected against erroneous power-stage turn on due to parasitic gate charging when power supplies are applied. Thus, voltage-supply ramp rates (dV/dt) are non-critical within the specified range (see the *Recommended Operating Conditions* table of this data sheet).

10.2 Bootstrap Supply

For a properly functioning bootstrap circuit, a small ceramic capacitor must be connected from each bootstrap pin (BST_X) to the power-stage output pin (OUT_X). When the power-stage output is low, the bootstrap capacitor is charged through an internal diode connected between the gate-drive power-supply pin (GVDD_X) and the bootstrap pin. When the power-stage output is high, the bootstrap capacitor potential is shifted above the output potential and thus provides a suitable voltage supply for the high-side gate driver. In an application with PWM switching frequencies in the range from 300 kHz to 400 kHz, TI recommends using 33-nF ceramic capacitors, size 0603 or 0805, for the bootstrap supply. These 33-nF capacitors ensure sufficient energy storage, even during minimal PWM duty cycles, to keep the high-side power stage FET (LDMOS) fully turned on during the remaining part of the PWM cycle.

版权 © 2017, Texas Instruments Incorporated

11 Layout

11.1 Layout Guidelines

These requirements must be followed to achieve best performance and reliability and minimum ground bounce at rated output power of TAS5634.

11.1.1 PCB Material Recommendation

FR-4 Glass Epoxy material with 1oz. (35 μm) copper is recommended for use with the TAS5634. The use of this material can provide for higher power output, improved thermal performance and better EMI margin (due to lower PCB trace inductance).

11.1.2 PVDD Capacitor Recommendation

The large capacitors used in conjunction with each full-bridge, are referred to as the PVDD Capacitors. These capacitors should be selected for proper voltage margin and adequate capacitance to support the power requirements. In practice, with a well designed system power supply, 1000 μF, 75 V bulk capacitors should support most applications. The PVDD capacitors should be low ESR type because they are used in a circuit associated with high-speed switching.

11.1.3 Decoupling Capacitor Recommendation

To design an amplifier that has robust performance, passes regulatory requirements, and exhibits good audio performance, good quality decoupling capacitors should be used. In practice, X5R or better should be used in this application.

The voltage of the decoupling capacitors should be selected in accordance with good design practices. Temperature, ripple current, and voltage overshoot must be considered. This fact is particularly true in the selection of the close decoupling capacitor that is placed on the power supply to each half-bridge. It must withstand the voltage overshoot of the PWM switching, the heat generated by the amplifier during high power output, and the ripple current created by high power output. A minimum voltage rating of 100V is required for use with a 58 V power supply.

See the TAS5634EVM User's Guide for more details including layout and bill-of-material.

11.1.4 Circuit Component Requirements

A number of circuit components are critical to performance and reliability. They include LC filter inductors and capacitors, decoupling capacitors and the heatsink. The best detailed reference for these is the TAS5634EVM BOM in the user's guide, which includes components that meet all the following requirements.

- **High frequency decoupling capacitors** - small high frequency decoupling capacitors are placed next to the IC to control switching spikes and keep high frequency currents in a tight loop to achieve best performance and reliability and EMC. They must be high quality ceramic parts with material like X7R or X5R and voltage ratings at least 30% greater than PVDD, to minimize loss of capacitance caused by applied DC voltage. (Capacitors made of materials like Y5V or Z5U should never be used in decoupling circuits or audio circuits because their capacitance falls dramatically with applied DC and AC voltage, often to 20% of rated value or less.)
- **Bulk decoupling capacitors** - large bulk decoupling capacitors are placed as close as possible to the IC to stabilize the power supply at lower frequencies. They must be high quality aluminum parts with low ESR and ESL and voltage ratings at least 25% more than PVDD to handle power supply ripple currents and voltages.
- **LC filter inductors** - to maintain high efficiency, short circuit protection and low distortion, LC filter inductors must be linear to at least the OCP limit and must have low DC resistance and core losses. For SCP, minimum working inductance, including all variations of tolerance, temperature and current level, must be 5μH. Inductance variation of more than 1% over the output current range can cause increased distortion.
- **LC filter capacitors** - to maintain low distortion and reliable operation, LC filter capacitors must be linear to twice the peak output voltage. For reliability, capacitors must be rated to handle the audio current generated in them by the maximum expected audio output voltage at the highest audio frequency.
- **Heatsink** - The heatsink must be fabricated with the PowerPAD™ contact area spaced 1.0mm +/-0.01mm above mounting areas that contact the PCB surface. It must be supported mechanically at each end of the IC. This mounting ensures the correct pressure to provide good mechanical, thermal and electrical contact with

Layout Guidelines (接下页)

TAS5634 PowerPAD™. The PowerPAD™ contact area must be bare and must be interfaced to the PowerPAD™ with a thin layer (about 1mil) of a thermal compound with high thermal conductivity.

11.1.5 Printed Circuit Board Requirements

PCB layout, audio performance, EMC and reliability are linked closely together, and solid grounding improves results in all these areas. The circuit produces high, fast-switching currents, and care must be taken to control current flow and minimize voltage spikes and ground bounce at IC ground pins. Critical components must be placed for best performance and PCB traces must be sized for the high audio currents that the IC circuit produces.

- **Grounding** - ground planes must be used to provide the lowest impedance and inductance for power and audio signal currents between the IC and its decoupling capacitors, LC filters and power supply connection. The area directly under the IC should be treated as central ground area for the device, and all IC grounds must be connected directly to that area. A matrix of vias must be used to connect that area to the ground plane. Ground planes can be interrupted by radial traces (traces pointing away from the IC), but they must never be interrupted by circular traces, which disconnect copper outside the circular trace from copper between it and the IC. Top and bottom areas that do not contain any power or signal traces should be flooded and connected with vias to the ground plane.
- **Decoupling capacitors** - high frequency decoupling capacitors must be located within 2mm of the IC and connected directly to PVDD and GND pins with solid traces. Vias must not be used to complete these connections, but several vias must be used at each capacitor location to connect top ground directly to the ground plane. Placement of bulk decoupling capacitors is less critical, but they still must be placed as close as possible to the IC with strong ground return paths. Typically the heatsink sets the distance.
- **LC filters** - LC filters must be placed as close as possible to the IC after the decoupling capacitors. The capacitors must have strong ground returns to the IC through top and bottom grounds for effective operation.
- **PCB** - PCB copper must be at least 1 ounce thickness. PVDD and output traces must be wide enough to carry expected average currents without excessive temperature rise. PWM input traces must be kept short and close together on the input side of the IC and must be shielded with ground flood to avoid interference from high power switching signals.
- **Heat sink -** The heatsink must be grounded well to the PCB near the IC, and a thin layer of highly conductive thermal compound (about 1mil) must be used to connect the heatsink to the PowerPAD™.

版权 © 2017, Texas Instruments Incorporated

11.2 Layout Example

Note T1: Bottom and top layer ground plane areas are used to provide strong ground connections. The area under the IC must be treated as central ground, with IC grounds connected there and a strong via matrix connecting the area to bottom ground plane. The ground path from the IC to the power supply ground through top and bottom layers must be strong to provide very low impedance to high power and audio currents.

Note T2: Low impedance X7R or X5R ceramic high frequency decoupling capacitors must be placed within 2mm of PVDD and GND pins and connected directly to them and to top ground plane to provide good decoupling of high frequency currents for best performance and reliability. Their DC voltage rating must be 2 times PVDD.

Note T3: Low impedance electrolytic bulk decoupling capacitors must be placed as close as possible to the IC. Typically the heat sink sets the distance. Wide PVDD traces are routed on the top layer with direct connections to the pins, without going through vias.

Note T4: LC filter inductors and capacitors must be placed as close as possible to the IC after decoupling capacitors. Inductors must have low DC resistance and switching losses and must be linear to at least the OCP (over current protection) limit. Capacitors must be linear to at least twice the maximum output voltage and must be capable of conducting currents generated by the maximum expected high frequency output.

Note T5: Bulk decoupling capacitors and LC filter capacitors must have strong ground return paths through ground plane to the central ground area under the IC.

Note T6: The heat sink must have a good thermal and electrical connection to PCB ground and to the IC PowerPAD™. It must be connected to the PowerPad through a thin layer, about 1 mil, of highly conductive thermal compound.

图 35. Printed Circuit Board - Top Layer

Layout Example (接下页)

Note B1: A wide PVDD bus and a wide ground path must be used to provide very low impedance to high power and audio currents to the power supply. Top and bottom ground planes must be connected with vias at many points to reinforce the ground connections.

Note B2: Wide output traces can be routed on the bottom layer and connected to output pins with strong via arrays.

图 36. Printed Circuit Board - Bottom Layer

版权 © 2017, Texas Instruments Incorporated

12 器件和文档支持

12.1 接收文档更新通知

要接收文档更新通知，请转至 TI.com 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 ***TI 的工程师对工程师 (E2E) 社区。***此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 ***TI 参考设计支持*** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.3 商标

PowerPAD, PurePath, E2E are trademarks of Texas Instruments.

12.4 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据如有变更，恕不另行通知和修订此文档。如欲获取此产品说明书的浏览器版本，请参阅左侧的导航。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TAS5634DDV	Active	Production	HTSSOP (DDV) | 44	35 | TUBE	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634
TAS5634DDV.A	Active	Production	HTSSOP (DDV) | 44	35 | TUBE	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634
TAS5634DDV.B	Active	Production	HTSSOP (DDV) | 44	35 | TUBE	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634
TAS5634DDVR	Active	Production	HTSSOP (DDV) | 44	2000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634
TAS5634DDVR.A	Active	Production	HTSSOP (DDV) | 44	2000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634
TAS5634DDVR.B	Active	Production	HTSSOP (DDV) | 44	2000 | LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	0 to 70	TAS5634

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TAS5634DDVR	HTSSOP	DDV	44	2000	330.0	24.4	8.6	15.6	1.8	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TAS5634DDVR	HTSSOP	DDV	44	2000	350.0	350.0	43.0

TUBE

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TAS5634DDV	DDV	HTSSOP	44	35	530	11.89	3600	4.9
TAS5634DDV.A	DDV	HTSSOP	44	35	530	11.89	3600	4.9
TAS5634DDV.B	DDV	HTSSOP	44	35	530	11.89	3600	4.9

DDV 44 PowerPAD™ TSSOP - 1.2 mm max height

PLASTIC SMALL OUTLINE

Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.
5. The exposed thermal pad is designed to be attached to an external heatsink.
6. Features may differ or may not be present.

LAND PATTERN EXAMPLE
SCALE:6X

SOLDER MASK DETAILS
NOT TO SCALE

4218830/A 08/2016

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE :6X

4218830/A 08/2016

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、与某特定用途的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保法规或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。对于因您对这些资源的使用而对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，您将全额赔偿，TI 对此概不负责。

TI 提供的产品受 TI 销售条款)、TI 通用质量指南 或 ti.com 上其他适用条款或 TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。 除非德州仪器 (TI) 明确将某产品指定为定制产品或客户特定产品，否则其产品均为按确定价格收入目录的标准通用器件。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

版权所有 © 2025，德州仪器 (TI) 公司

最后更新日期：2025 年 10 月